

# 150mA CMOS LDO Regulator



#### **FEATURES**

- Guaranteed 150mA output current
- Low dropout voltage of 90mV typical at 150mA
- Stable with 1µF ceramic output capacitor
- External 10nF bypass capacitor for low noise
- Quick-start feature
- No-load ground current of 55µA typical
- Full-load ground current of 80µA typical
- ±1.0% output voltage initial accuracy
- ±2.0% accuracy over temperature
- "Zero" current shutdown mode
- Current limit and Under voltage lockout
- Thermal protection
- Thin SOT23-5 package

#### **APPLICATIONS**

- Cellular phones
- Battery-powered devices
- Consumer Electronics

#### DESCRIPTION

The CAT6217 is a 150mA CMOS low dropout regulator that provides fast response time during load current and line voltage changes.

The quick-start feature allows the use of an external bypass capacitor to reduce the overall output noise without affecting the turn-on time of just 150µs.

With zero shutdown current and low ground current of 55µA typical, the CAT6217 is ideal for battery-operated devices with supply voltages from 2.3V to 5.5V. An internal under voltage lockout circuit disables the output at supply voltages under 2.1V typical.

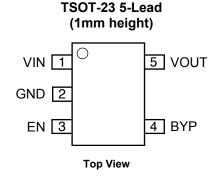
The CAT6217 offers 1% initial accuracy and low dropout voltage, 90mV typical at 150mA. Stable operation is provided with a 1 $\mu$ F ceramic capacitor, reducing required board space and component cost.

Other features include output short-circuit current limit and thermal protection.

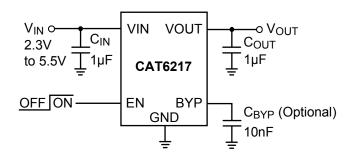
The device is available in the low profile (1mm max height) 5-lead thin SOT23 package.

For Ordering Information details, see page 9.

#### PIN CONFIGURATION



#### TYPICAL APPLICATION CIRCUIT



1



#### PIN DESCRIPTIONS

Pin#	Name	Function	
1	VIN	Supply voltage input.	
2	2 GND Ground reference.		
3	EN	Enable input (active high); a $2.5M\Omega$ pull-down resistor is provided.	
4	BYP	Optional bypass capacitor connection for noise reduction and PSRR enhancing.	
5	VOUT	LDO Output Voltage.	

#### **BLOCK DIAGRAM**

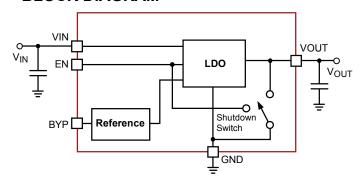


Figure 2. CAT6217 Functional Block Diagram

#### **PIN FUNCTION**

**VIN** is the supply pin for the LDO. A small 1 $\mu$ F ceramic bypass capacitor is required between the V<sub>IN</sub> pin and ground near the device. When using longer connections to the power supply, C<sub>IN</sub> value can be increased without limit. The operating input voltage range is from 2.3V to 5.5V.

**EN** is the enable control logic (active high) for the regulator output. It has a  $2.5 \text{M}\Omega$  pull-down resistor, which assures that if EN pin is left open, the circuit is disabled.

**VOUT** is the LDO regulator output. A small  $1\mu F$  ceramic bypass capacitor is required between the  $V_{OUT}$  pin and ground for stability. For better transient response, its value can be increased to  $4.7\mu F$ .

The capacitor should be located near the device. ESR domain is  $5m\Omega$  to  $500m\Omega$ .  $V_{OUT}$  can deliver a maximum guaranteed current of 150mA. A  $250\Omega$  internal shutdown switch discharges the output capacitor in the no-load condition.

**GND** is the ground reference for the LDO. The pin must be connected to the ground plane on the PCB.

BYP is the reference bypass pin. An optional  $0.01\mu F$  capacitor can be connected between BYP pin and GND to reduce the output noise and enhance the PSRR at high frequency.

# ABSOLUTE MAXIMUM RATINGS (1)

Parameter	Rating	Unit
V <sub>IN</sub>	0 to 6.5	V
$V_{EN}, V_{OUT}$	-0.3 to V <sub>IN</sub> +0.3	V
Junction Temperature, T <sub>J</sub>	+150	°C
Power Dissipation, P <sub>D</sub>	Internally Limited (2)	mW
Storage Temperature Range, T <sub>S</sub>	-65 to +150	°C
Lead Temperature (soldering, 5 sec.)	260	°C
ESD Rating (Human Body Model)	3	kV

# **RECOMMENDED OPERATING CONDITIONS (3)**

Parameter	Range	Unit
V <sub>IN</sub>	2.3 to 5.5	V
V <sub>EN</sub>	0 to V <sub>IN</sub>	V
Junction Temperature Range, T <sub>J</sub>	-40 to +125	°C
Package Thermal Resistance (SOT23-5), $\theta_{JA}$	235	°C/W

Typical application circuit with external components is shown on page 1.

- (1) Exceeding maximum rating may damage the device
- (2) The maximum allowable power dissipation at any T<sub>A</sub> (ambient temperature) is P<sub>Dmax</sub> = (T<sub>Jmax</sub> T<sub>A</sub>)/θ<sub>JA</sub>. Exceeding the maximum allowable power dissipation will result in excessive die temperature, and the regulator will go into thermal shutdown.
- (3) The device is not guaranteed to work outside its operating rating.



# **ELECTRICAL OPERATING CHARACTERISTICS** (1)

 $V_{IN} = V_{OUT} + 1.0V$ ,  $V_{EN} = High$ ,  $I_{OUT} = 100 \mu A$ ,  $C_{IN} = C_{OUT} = 1 \mu F$ , ambient temperature of 25°C (over recommended operating conditions unless specified otherwise). **Bold numbers** apply for the entire junction temperature range.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
V	Output Voltage Accuracy	Initial accuracy	-1.0		+1.0	%	
V <sub>OUT-ACC</sub>	Output Voltage Accuracy	Initial accuracy	-2.0		+2.0		
TC <sub>OUT</sub>	Output Voltage Temp. Coefficient			40		ppm/°C	
V <sub>R-LINE</sub>	Line Regulation	V <sub>IN</sub> = V <sub>OUT</sub> + 1.0V to 5.5V	-0.2	±0.1	+0.2	%/V	
	Line Regulation		-0.4		+0.4		
,, .	Load Regulation	I <sub>OUT</sub> = 100μA to 150 mA		0.6	1.0	%	
$V_{R-LOAD}$		10UT - 100µA to 130 MA			1.3		
V	Dropout Voltage (2)	1 - 450m A		90	125	m\/	
$V_{DROP}$	Dropout Voltage	I <sub>OUT</sub> = 150mA			150	- mV	
	Ground Current	I <sub>OUT</sub> = 0μA		55	75	μA	
I <sub>GND</sub> (		Ιουτ – υμΑ			90		
		I <sub>OUT</sub> = 150mA		80			
I <sub>GND-SD</sub>	Shutdown Ground Current	V <sub>EN</sub> < 0.4V			1	μΑ	
					2		
PSRR	Power Supply Rejection Ratio	$f = 1kHz$ , $C_{BYP} = 10nF$		64		dB	
FORK		$f = 20kHz, C_{BYP} = 10nF$		54			
I <sub>SC</sub>	Output short circuit current limit	V <sub>OUT</sub> = 0V		350		mA	
$T_{ON}$	Turn-On Time	C <sub>BYP</sub> = 10nF		150		μs	
$e_N$	Output Noise Voltage (3)	BW = 10Hz to 100kHz		45		μVrms	
R <sub>OUT-SH</sub>	Shutdown Switch Resistance			250		Ω	
R <sub>EN</sub>	Enable pull-down resistor			2.5		ΜΩ	
$V_{\text{UVLO}}$	Under-voltage lock out (UVLO) threshold			2.1		V	
ESR	C <sub>OUT</sub> equivalent series resistance		5		500	mΩ	
Enable Ir	nput						
V <sub>HI</sub>	Logic High Level	V <sub>IN</sub> = 2.3 to 5.5V	1.8			V	
$V_{LO}$	Logic Low Level	V <sub>IN</sub> = 2.3 to 5.5V			0.4	V	
I <sub>EN</sub>	Enable Input Current	V <sub>EN</sub> = 0.4V		0.15	1	μΑ	
	Enable Input Current	V <sub>EN</sub> = V <sub>IN</sub>		1.5	4		
Thermal Protection							
T <sub>SD</sub>	Thermal Shutdown			160		°C	
T <sub>HYS</sub>	Thermal Hysteresis			10		°C	

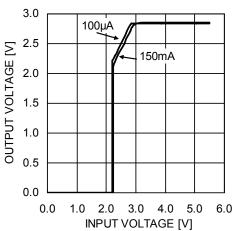
- (1 Specification for 2.85V output version unless specified otherwise.
- (2) Dropout voltage is defined as the input-to-output differential at which the output voltage drops 2% below its nominal value measured at 1V differential. During test, the input voltage stays always above the minimum 2.3V.
- (3) Specification for 1.8V output version.

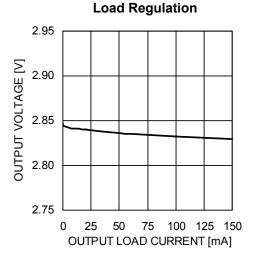


#### TYPICAL CHARACTERISTICS (shown for 2.85V output version)

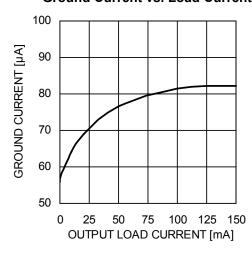
 $V_{IN}$  = 3.85V,  $I_{OUT}$  = 100 $\mu$ A,  $C_{IN}$  =  $C_{OUT}$  = 1 $\mu$ F,  $C_{BYP}$  = 10nF,  $T_A$  = 25°C unless otherwise specified.

# **Dropout Characteristics**

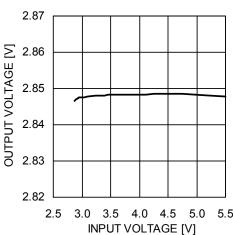




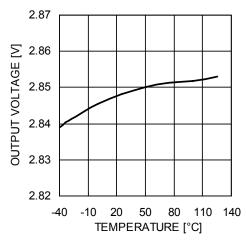
#### **Ground Current vs. Load Current**



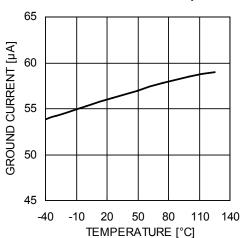
### **Line Regulation**



#### **Output Voltage vs. Temperature**



#### **Ground Current vs. Temperature**

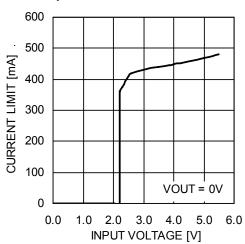


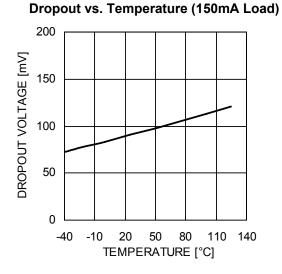


#### TYPICAL CHARACTERISTICS (shown for 2.85V output option)

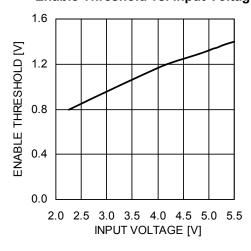
 $V_{IN}$  = 3.85V,  $I_{OUT}$  = 100 $\mu$ A,  $C_{IN}$  =  $C_{OUT}$  = 1 $\mu$ F,  $C_{BYP}$  = 10nF,  $T_A$  = 25°C unless otherwise specified.

#### **Output Short-Circuit Current Limit**

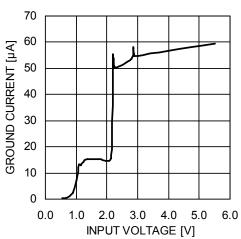




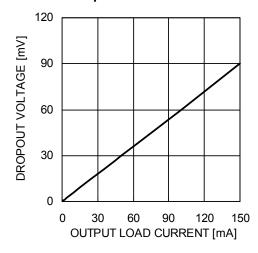
#### **Enable Threshold vs. Input Voltage**



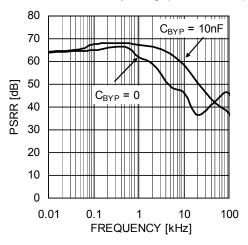
#### **Ground Current vs. Input Voltage**



#### **Dropout vs. Load Current**



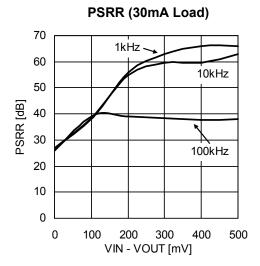
#### PSRR vs. Frequency (10mA Load)

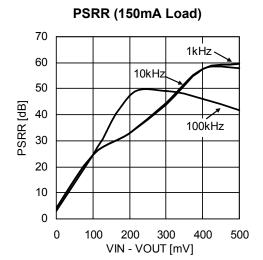




#### TYPICAL CHARACTERISTICS (shown for 2.85V output option)

 $V_{IN}$  = 3.85V,  $I_{OUT}$  = 100 $\mu$ A,  $C_{IN}$  =  $C_{OUT}$  = 1 $\mu$ F,  $C_{BYP}$  = 10nF,  $T_A$  = 25°C unless otherwise specified.



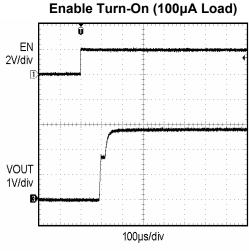


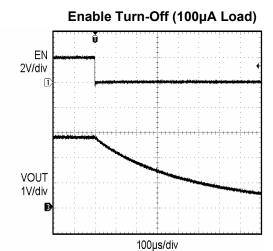


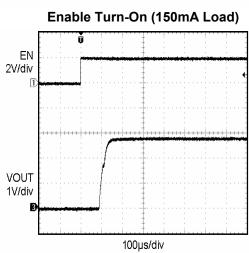
## TRANSIENT CHARACTERISTICS (shown for 2.85V output option)

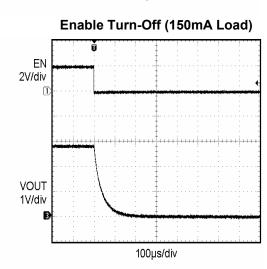
 $V_{IN}$  = 3.85V,  $I_{OUT}$  = 100 $\mu$ A,  $C_{IN}$  =  $C_{OUT}$  = 1 $\mu$ F,  $C_{BYP}$  = 10nF,  $T_A$  = 25°C unless otherwise specified.

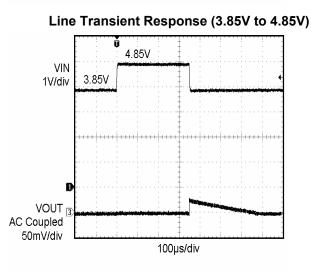
Note: All transient characteristics are generated using the evaluation board CAT621XEVAL1.

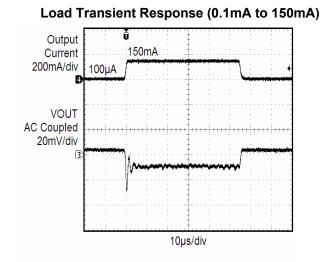










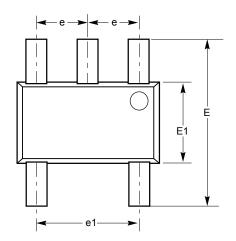


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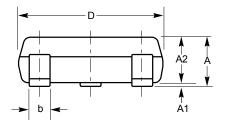


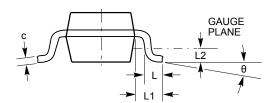
## **PACKAGE OUTLINES**

# 5-LEAD TSOT-23 (1)(2)



SYMBOL	MIN	NOM	MAX
Α	_	_	1.00
A1	0.01	0.05	0.10
A2	0.80	0.87	0.90
b	0.30	_	0.45
С	0.12	0.15	0.20
D	2.90 BSC		
Е	2.80 BSC		
E1	1.60 BSC		
е	0.95 BSC		
e1	1.90 BSC		
L	0.30	0.40	0.50
L1	0.60 REF		
L2	0.25 BSC		
θ	0°		8°



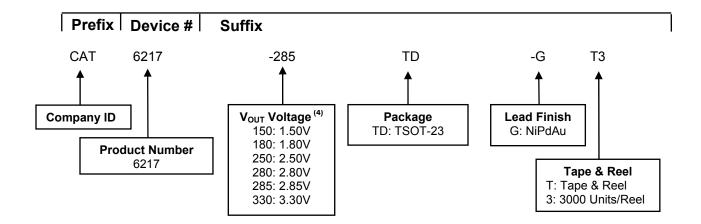


2HFor current Tape and Reel information, download the PDF file from:

- (1) All dimensions are in millimeters, angles in degrees.
- (2) Refer JEDEC MO-193.



#### **EXAMPLE OF ORDERING INFORMATION**



Ordering Number	V <sub>OUT</sub> Voltage	Package	Quantity per Reel
CAT6217-150TD-GT3	1.50V	TSOT-23	3000
CAT6217-180TD-GT3	1.80V	TSOT-23	3000
CAT6217-250TD-GT3	2.50V	TSOT-23	3000
CAT6217-280TD-GT3	2.80V	TSOT-23	3000
CAT6217-285TD-GT3	2.85V	TSOT-23	3000
CAT6217-330TD-GT3 (4)	3.30V	TSOT-23	3000

- (1) All packages are RoHS-compliant (Lead-free, Halogen-free).
- (2) The standard finish is NiPdAu.
- (3) The device used in the above example is a CAT6217-285TD-GT3 (V<sub>OUT</sub> = 2.85V, in an TSOT-23 package, NiPdAu, Tape and Reel, 3000 units).
- (4) Standard voltages are 1.50V, 1.80V, 2.50V, 2.80V, and 2.85V. For other voltage options, please contact your nearest Catalyst Semiconductor Sales office.
- (5) Top marking for CAT6217 is RT.

#### REVISION HISTORY

Date	Rev.	Reason
06/21/2007	Α	Preliminary Revision

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